



PJM138NSA

N- Enhancement Mode Field Effect Transistor

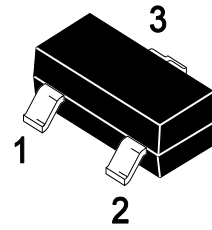
Features

- Low gate charge and $R_{DS(ON)}$
- Rugged and reliable

Application

- Direct logic-level interface: TTL/CMOS
- Drivers: relays, solenoids, lamps, hammers, Display, memories, transistors, etc.
- Battery operated systems
- Solid-state relays

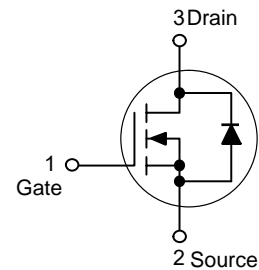
SOT-23



1. Gate 2. Source 3. Drain

Marking: S3

Schematic diagram



Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current-Continuous	I_D	0.22	A
Maximum Power Dissipation	P_D	0.35	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	$^{\circ}\text{C}$

Thermal Characteristics

Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	357	$^{\circ}\text{C/W}$
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**Electrical Characteristics** ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Units
Static Characteristics						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	50			V
Drain to Source Leakage Current	I_{DSS}	$V_{DS} = 50V, V_{GS} = 0V$			0.5	μA
		$V_{DS} = 30V, V_{GS} = 0V$			100	nA
Gate-body leakage current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 200	nA
Gate threshold voltage ^{Note1}	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1	1.6	2	V
Drain-source on-resistance ^{Note1}	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 0.22A$		1	3.5	Ω
		$V_{GS} = 4.5V, I_D = 0.22A$		1.1	6	Ω
Forward tranconductance ^{Note1}	g_{FS}	$V_{DS} = 10V, I_D = 0.22A$		0.13		S
Dynamic characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 25V, V_{GS} = 0V, f = 1MHz$		26.5		pF
Output Capacitance	C_{oss}			12.9		
Reverse Transfer Capacitance	C_{rss}			5.9		
Switching Characteristics						
Turn-on delay time	$t_{d(on)}$	$V_{GS} = 10V, V_{DD} = 30V, I_D = 0.29A$ $, R_{GEN} = 6\Omega,$			5	ns
Turn-on rise time	t_r				18	
Turn-off delay time	$t_{d(off)}$				36	
Turn-off fall time	t_f				14	
Source-Drain Diode characteristics						
Diode Forward voltage ^{Note1}	V_{SD}	$V_{GS} = 0V, I_S = 0.44A$			1.4	V

Notes :

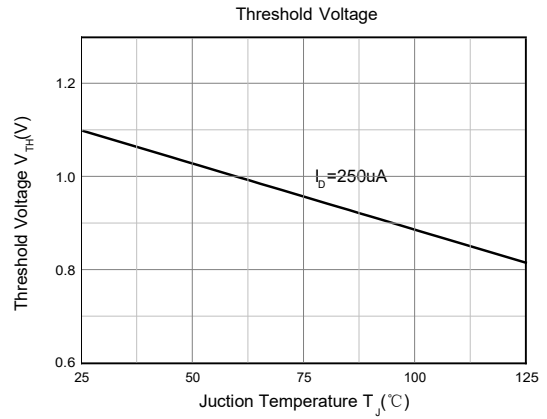
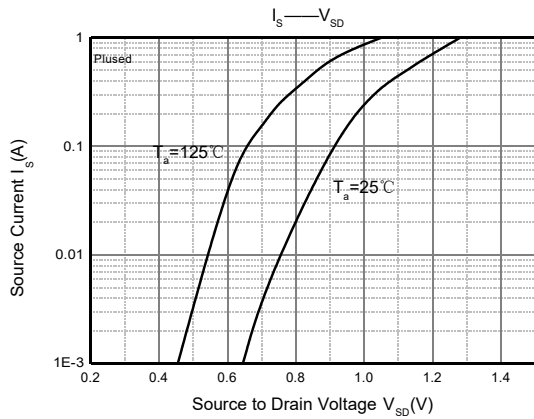
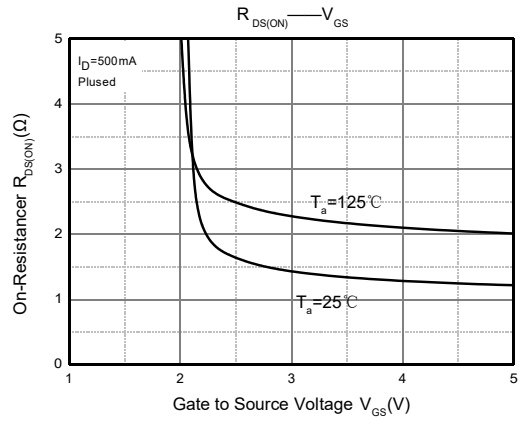
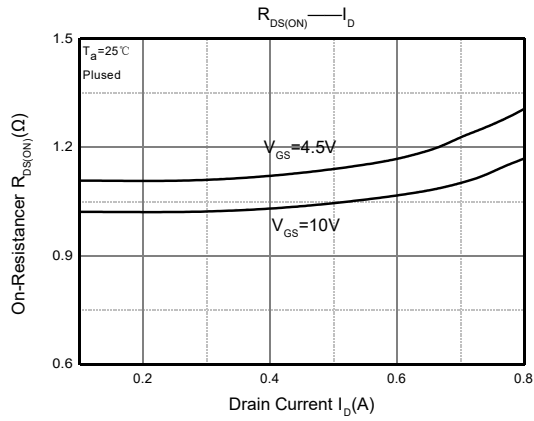
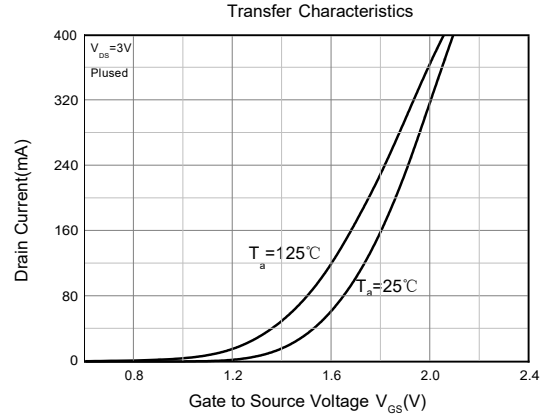
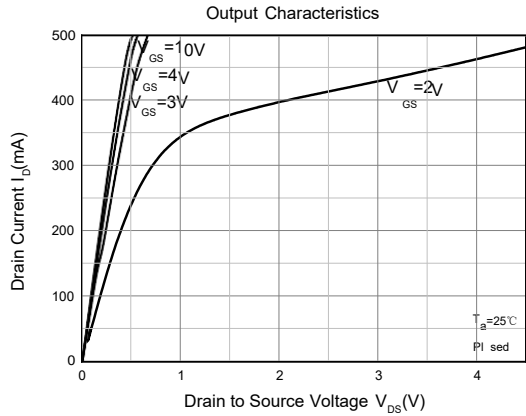
1. Pulse test : pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.



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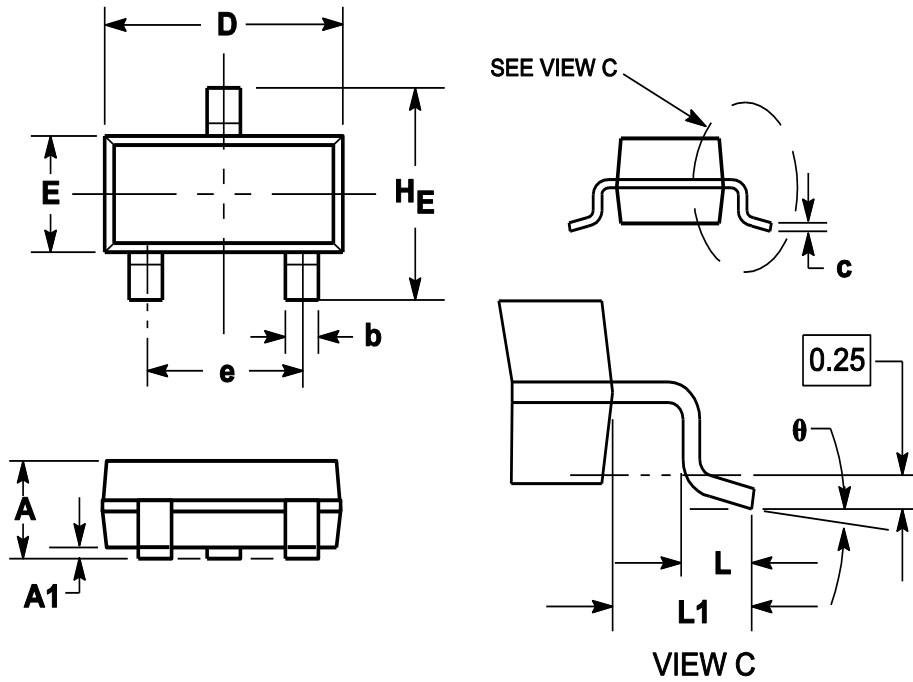
Typical Characteristic Curves



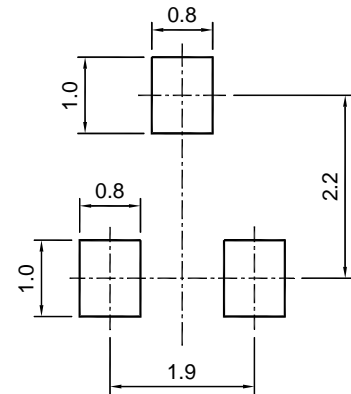


Package Outline

SOT-23



Symbol	Dimensions in millimeter		
	Min.	Typ.	Max.
A	0.900	1.025	1.150
A1	0.000	0.050	0.100
b	0.300	0.400	0.500
c	0.080	0.115	0.150
D	2.800	2.900	3.000
E	1.200	1.300	1.400
HE	2.250	2.400	2.550
e	1.800	1.900	2.000
L1	0.550REF		
L	0.300		0.500
θ	0°		8°



SOT-23 (TO-236)

Recommended soldering pad

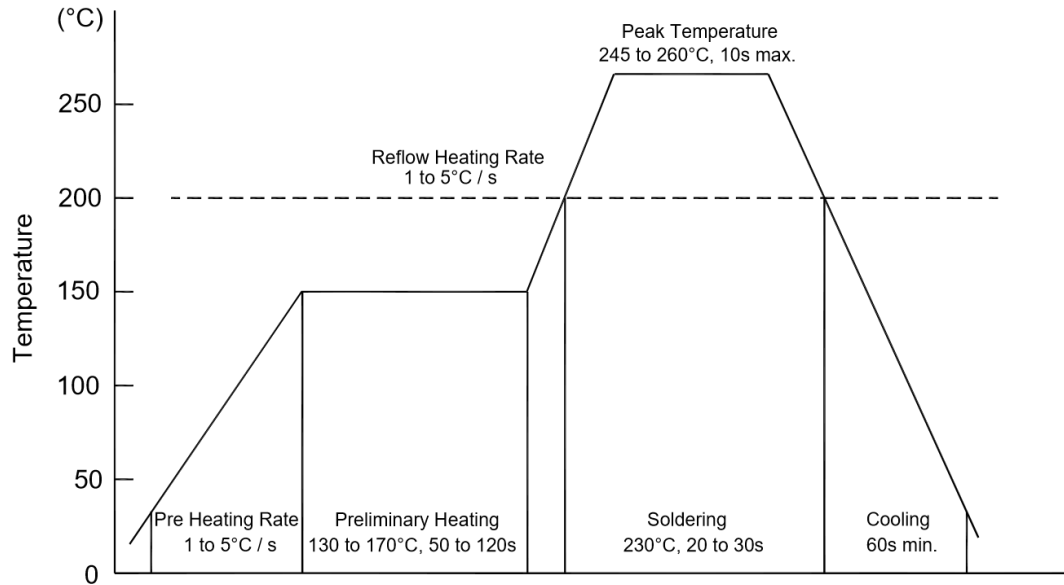
Ordering Information

Device	Package	Shipping
PJM138NSA	SOT-23	3000PCS/Reel&Tape



Conditions of Soldering and Storage

◆ Recommended condition of reflow soldering



Recommended peak temperature is over 245 °C. If peak temperature is below 245 °C, you may adjust the following parameters:

- Time length of peak temperature (longer)
- Time length of soldering (longer)
- Thickness of solder paste (thicker)

◆ Conditions of hand soldering

- Temperature: 370 °C
- Time: 3s max.
- Times: one time

◆ Storage conditions

- **Temperature**
5 to 40 °C
- **Humidity**
30 to 80% RH
- **Recommended period**
One year after manufacturing



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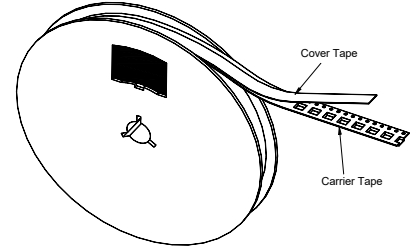
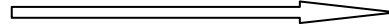
Package Specifications

◆ The method of packaging

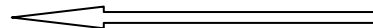
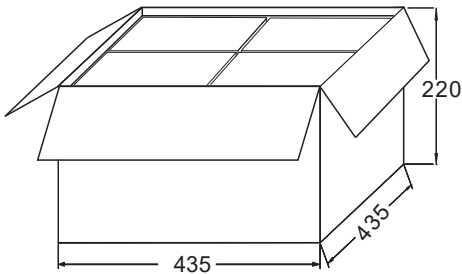
SOT-23 (TO-236)



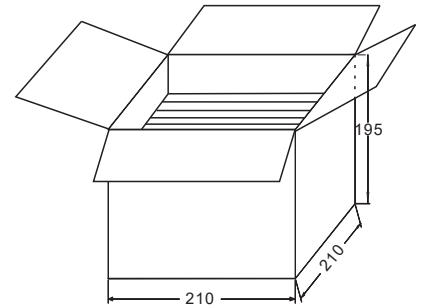
3,000 pcs per reel



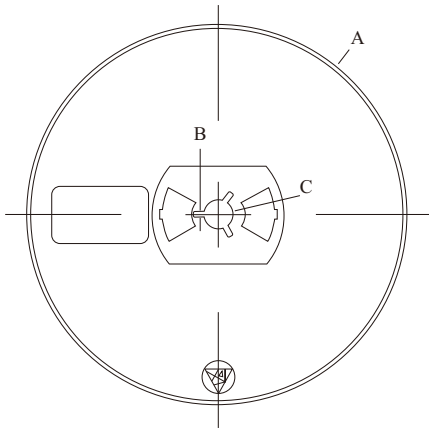
30,000 pcs per box
10 reels per box



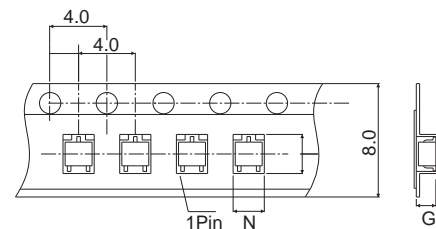
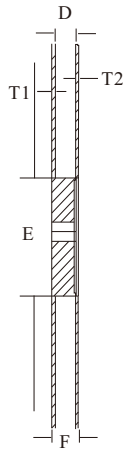
120,000 pcs per carton
4 boxes per carton



◆ Embossed tape and reel data



Reel (7")



Tape (8mm)

Symbol	Value (unit: mm)
A	Ø 177.8±1
B	2.7±0.2
C	Ø 13.5±0.2
E	Ø 54.5±0.2
F	12.3±0.3
D	9.6+2/-0.3
T1	1.0±0.2
T2	1.2±0.2
N	3.15±0.1
G	1.25±0.1

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